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RoHS

COMPLIANT

Phase Control Thyristor RMS SCRs, 25 A, 35 A



TO-48 (TO-208AA)
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PRIMARY CHARACTERISTICS					
I _{T(AV)}	16 A, 22 A				
I _{T(RMS)}	25 A, 35 A				
V _{DRM} /V _{RRM}	25 V, 50 V, 100 V, 150 V, 200 V, 250 V, 300 V, 400 V, 500 V, 600 V, 700 V, 800 V, 1000 V 1200 V				
V _{TM}	2.3 V				
I _{GT}	60 mA				
TJ	-40 °C to +125 °C				
Package	TO-48 (TO-208AA)				
Circuit configuration	Single SCR				

FEATURES

- General purpose stud mounted
- Broad forward and reverse voltage range through 1200 V
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

MAJOR RATINGS AND CHARACTERISTICS						
PARAMETER	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS		
1		16 ⁽¹⁾	22 (1)	А		
I _{T(AV)}	T _C	-65 to +65 ⁽¹⁾	-40 to +40	°C		
I _{T(RMS)}		25	35	А		
1	50 Hz	145	285	۸		
I _{TSM}	60 Hz	150 ⁽¹⁾	300 (1)	A		
l ² t	50 Hz	103	410	A ² s		
141	60 Hz	94	375	A-S		
I _{GT}		40	40	mA		
dV/dt		-	100 (1)	V/µs		
dl/dt		75 to 100	100	A/µs		
V _{DRM}	Range	25 to 800	600 to 1200	V		
V _{RRM}	Range	25 to 800	600 to 1200	V		
TJ		-65 to +125 ⁽¹⁾	-40 to +125 ⁽¹⁾	°C		

Note

(1) JEDEC[®] registered value

VS-2N681, VS-2N5205 Series



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ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS (APPLIED GATE VOLTAGE ZERO OR NEGATIVE)							
TYPE NUMBER	V _{RRM} /V _{DRM} , MAXIMUM REPETITIVE PEAK REVERSE AND OFF-STATE VOLTAGE V	V _{RSM} , MAXIMUM NON-REPETITIVE PEAK REVERSE VOLTAGE (t _p < 5 ms) V	Тј				
VS-2N681	25	35					
VS-2N682	50	75					
VS-2N683	100	150					
VS-2N684	150	200					
VS-2N685	200	300					
VS-2N686	250	350					
VS-2N687	300	400	-65 °C to +125 °C				
VS-2N688	400	500					
VS-2N689	500	600					
VS-2N690	600	720					
VS-2N691	700	840					
VS-2N692	800	960]				
VS-2N5205	800	960					
VS-2N5206	1000	1200	-40 °C to +125 °C				
VS-2N5207	1200	1440	1				

Note

• JEDEC registered values

PARAMETER	SYMBOL	TEST CON	DITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS
Maximum average on-state		100° half aine wave good	ation	16 ⁽¹⁾	22 ⁽¹⁾	Α
current at case temperature	I _{T(AV)}	180° half sine wave condu	CLION	-65 to +65 ⁽¹⁾	-40 to +40 ⁽¹⁾	°C
Maximum RMS on-state current	I _{T(RMS)}			25	35	А
		50 Hz half cycle sine wave or 6 ms rectangular pulse	Following any rated load condition, and	145	285	
Maximum peak, one-cycle non-repetitive surge current		60 Hz half cycle sine wave or 5 ms rectangular pulse	-	150 ⁽¹⁾	300 (1)	
	I _{TSM}	50 Hz half cycle sine wave Same conditions a or 6 ms rectangular pulse above except with		170	340	A
		60 Hz half cycle sine wave or 5 ms rectangular pulse	V _{RRM} applied following surge = 0	180	355	
		t = 10 ms Rated V _{BRM} applied		103	410	
Maximum I ² t capability for fusing	l ² t	t = 8.3 ms	following surge, initial T _J = 125 °C	94	375	A ² s
Maximum I ² t capability for		t = 10 ms	V _{RRM} = 0 following	145	580	
individual device fusing		t = 8.3 ms surge, initial T_J = 125 °C		135	530	
Maximum I ² \t capability for individual device fusing	l²√t (2)	t = 0.1 ms to 10 ms, initial $T_J < 125 \text{ °C}$ V _{RRM} applied following surge = 0		1450	5800	A²√s
Maximum peak on-state voltage	V _{TM}	$T_J = 25 \text{ °C}, I_{T(AV)} = 16 \text{ A} (50)$ $I_{T(AV)} = 22 \text{ A} (70 \text{ A peak}) 2 \text{ N}$	2 (1)	2.3 ⁽¹⁾	v	
Maximum holding current	I _H	Anode supply 24 V, initial I	20 at 25 °C (typical)	200 ⁽¹⁾ at -40 °C	mA	

Notes

⁽¹⁾ JEDEC registered value

⁽²⁾ I²t for time $t_x = I^2 \sqrt{t} \cdot \sqrt{t_x}$

Revision: 21-Sep-17

2



VS-2N681, VS-2N5205 Series

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SWITCHING					
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SWITCHING						
PARAME	TER	SYMBOL	TEST CONDITIONS	VALUES 2N681-92	VALUES 2N5205-07	UNITS
	V _{DM} = 25 V to 600 V		$T_C = 125 \text{ °C}, V_{DM} = \text{Rated } V_{DRM},$	100	-	
Maximum non-repetitive rate of rise of turned-on	V _{DM} = 700 V to 800 V	dl/dt	$I_{TM} = 2 \times dI/dt$, gate pulse = 20 V, 15 Ω , $t_p = 6 \mu s$, $t_r = 0.1 \mu s$ maximum Per JEDEC standard RS-397, 5.2.2.6	75	-	A∕µs
current		ai/at -	$ \begin{array}{l} T_{C} = 125 \ ^{\circ}\text{C}, \ V_{DM} = 600 \ V, \ I_{TM} = 200 \ A \ at \\ 400 \ Hz \ maximum, \ gate \ pulse = 20 \ V, \ 15 \ \Omega, \\ t_{p} = 6 \ \mu s, \ t_{r} = 0.1 \ \mu s \ maximum \\ \text{Per JEDEC standard RS-397, } 5.2.2.6 \end{array} $	-	100	7 μ3
Typical delay time		t _d	$\label{eq:T_C} \begin{array}{l} T_{C} = 25 \ ^{\circ}\text{C}, \ V_{DM} = \text{Rated} \ V_{DRM}, \ I_{TM} = 10 \ \text{A} \\ \text{DC resistive circuit, gate pulse} = 10 \ \text{V}, \\ 40 \ \Omega \ \text{source,} \ t_{p} = 6 \ \mu\text{s}, \ t_{r} = 0.1 \ \mu\text{s} \end{array}$	1	1	μs

BLOCKING

PAR	AMETER	SYMBOL	TEST CONDITIO	NS	VALUES 2N681-92	VALUES 2N5205-07	UNITS
Minimum critical rate	of	dV/dt	T _J = 125 °C, exponential to 100 % rated V _{DRM}	Gate open	100 (typical)	100 (1)	V/µs
rise of off-state voltag	ge	uv/ui	$T_J = 125 \text{ °C}$, exponential to 67 % rated V_{DRM}	circuited	250 (typical)	250	v/µs
	V_{RRM} , V_{DRM} = 400 V				3.5	-	
	V_{RRM} , V_{DRM} = 500 V				3.5	-	
Ma. 1	V_{RRM} , V_{DRM} = 600 V	I _{DRM} ,			2.5	3.3	
Maximum reverse leakage current	V _{RRM} , V _{DRM} = 700 V		T _J = 125 °C		2.2	-	mA
$\frac{V_{\text{RRM}}, V_{\text{DRM}} = 800 \text{ V}}{V_{\text{RRM}}, V_{\text{DRM}} = 1000 \text{ V}}$	I _{RRM}			2	2.5		
	V _{RRM} , V _{DRM} = 1000 V				-	2]
	V _{RRM} , V _{DRM} = 1200 V				-	1.7	1

Note

⁽¹⁾ JEDEC registered value

PARAMETER	SYMBOL		TEST CONDITIONS	VALUES	VALUES	UNITS
FANAMETEN	STWDUL		TEST CONDITIONS	2N681-92	2N5205-07	UNITS
Maximum peak gate power	P_{GM}		2N681 series; or 2N5204 series	5 (1)	60 ⁽¹⁾	w
Maximum average gate power	P _{G(AV)}			0.5 ⁽¹⁾	0.5 ⁽¹⁾	
Maximum peak positive gate current	+I _{GM}			2 (1)	2	Α
Maximum peak positive gate voltage	+V _{GM}			10 ⁽¹⁾	-	v
Maximum peak negative gate voltage	-V _{GM}			5 (1)	5 (1)	v
Maximum required DC gate		T _C = min. rated value	Maximum required gate trigger current is the lowest value which will trigger all units with + 6 V anode to cathode	80 (1)	80 (1)	
current to trigger	I _{GT}	T _C = 25 °C		40	40	mA
		T _C = 125 °C		18.5	20	
Typical DC gate current to trigger		T _C = 25 °C, +	6 V anode to cathode	30	30	
Maximum required DC gate voltage to trigger	V _{GT}	T _C = -65 °C	Maximum required gate trigger voltage is the lowest value which will trigger all units with + 6 V anode to cathode	3 (1)	3 (1)	v
		T _C = 25 °C		2	2	
Typical DC gate voltage to trigger		T _C = 25 °C, +	6 V anode to cathode	1.5	1.5	
Maximum DC gate voltage not to trigger	V _{GD}	T _C = 125 °C	Maximum gate voltage not to trigger is the maximum value which will not trigger any unit with rated V _{DRM} anode to cathode	0.25 ⁽¹⁾	0.25 ⁽¹⁾	v

Note

⁽¹⁾ JEDEC registered value

Revision: 21-Sep-17

VS-2N681, VS-2N5205 Series

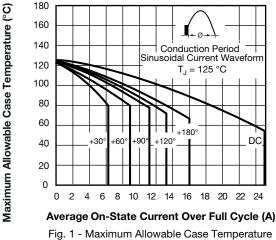


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THERMAL AND	THERMAL AND MECHANICAL SPECIFICATIONS									
PARAMETER		SYMBOL TEST CONDITIONS		VALUES 2N681-92	VALUES 2N5205-07	UNITS				
Operating junction and storage temperature rar	nge	T _J , T _{Stg}		-65 to 125 ⁽¹⁾	-40 to 125 ⁽¹⁾	°C				
Maximum internal therm junction to case	al resistance,	R _{thJC}	DC operation	1.5	1.5 ⁽¹⁾	°C/W				
Typical thermal resistan case to sink	ce,	R _{thCS}	Mounting surface, smooth, flat and greased	0.35	0.35	0/10				
to nut Mounting torque ± 10 % to device			L. I. Sector data sector	20 (27.5)		lbf · in				
			Lubricated threads (Non-lubricated threads)	0.23 (0.32)		kgf∙cm				
			(Non-lubicated threads)		2.3 (3.1)					
					25					
		Lubricated threads		0.29		kgf · cm				
				2.8		N·m				
Approximate weight				14	14	g				
				0.49	0.5	oz.				
Case style				TO	-48 (TO-208AA)					

Note

⁽¹⁾ JEDEC registered value



vs. Average On-State Current, 2N681 Series

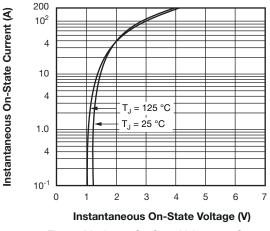
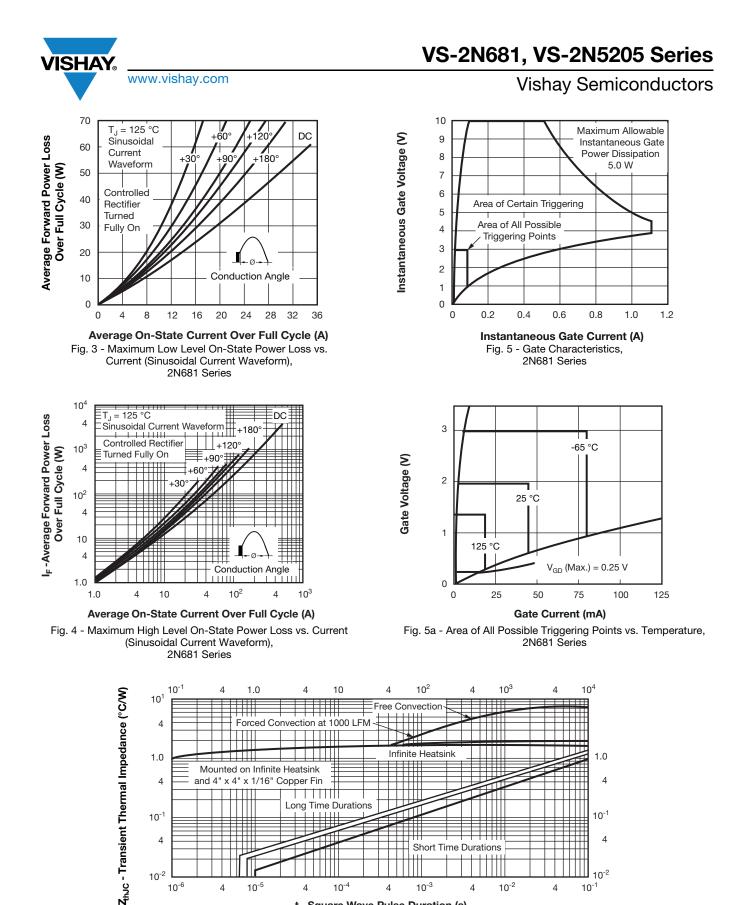
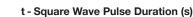
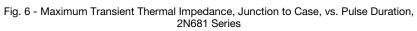
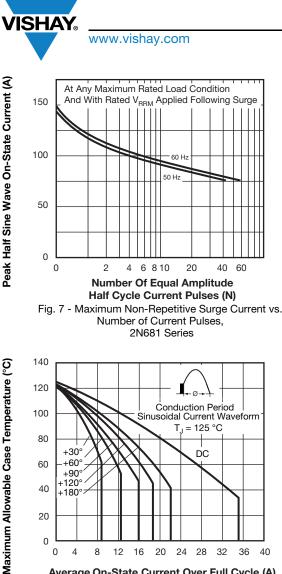


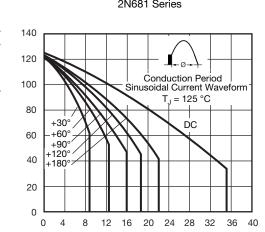
Fig. 2 - Maximum On-State Voltage vs. Current, 2N681 Series











Average On-State Current Over Full Cycle (A) Fig. 8 - Maximum Allowable Case Temperature vs. Average

On-State Current (Sinusoidal Current Waveform), 2N5205 Series

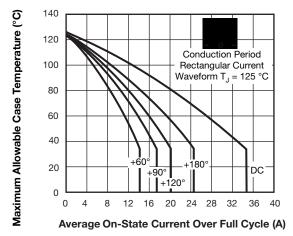


Fig. 9 - Maximum Allowable Case Temperature vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

VS-2N681, VS-2N5205 Series

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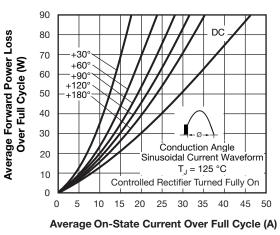


Fig. 10 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series

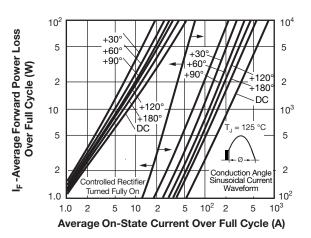
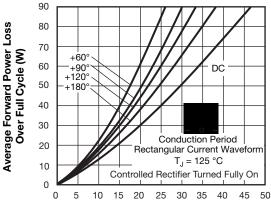


Fig. 11 - Maximum High-Level On-State Power Loss vs. Average On-State Current (Sinusoidal Current Waveform), 2N5205 Series



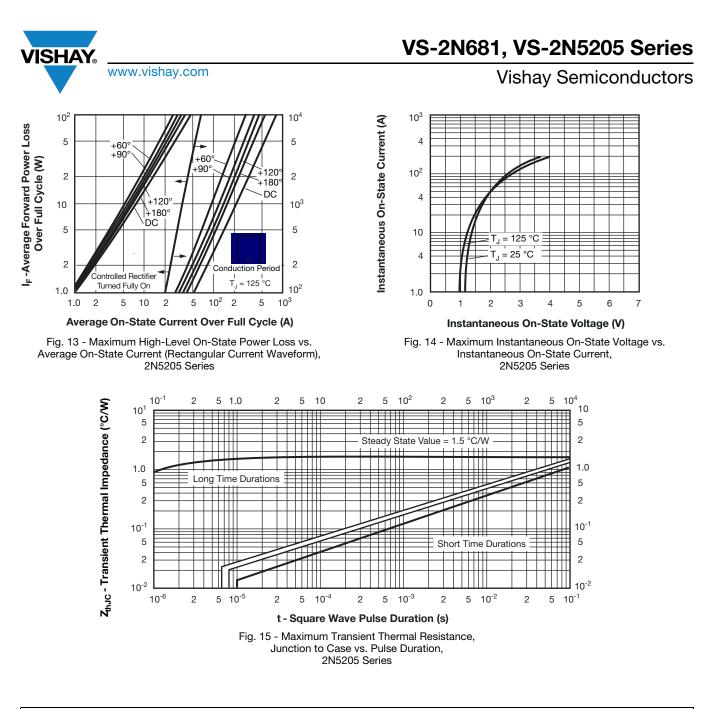
Average On-State Current Over Full Cycle (A)

Fig. 12 - Maximum Low-Level On-State Power Loss vs. Average On-State Current (Rectangular Current Waveform), 2N5205 Series

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